

MOSFET

OptiMOS™ 5 Power-Transistor, 150 V

Features

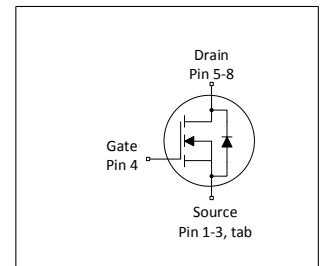
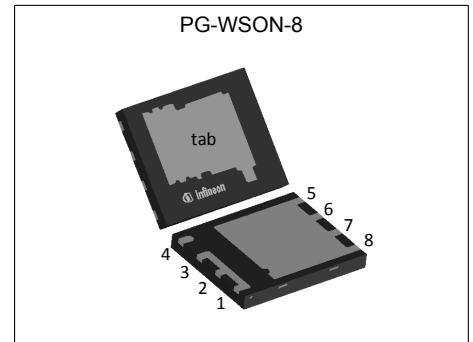
- Dual-side cooled package with lowest Junction-top thermal resistance
- N-channel, normal level
- Excellent gate charge x $R_{DS(on)}$ product (FOM)
- Very low on-resistance $R_{DS(on)}$
- 175 °C operating temperature
- Pb-free lead plating; RoHS compliant
- Ideal for high-frequency switching and synchronous rectification

Product validation

Fully qualified according to JEDEC for Industrial Applications

Table 1 Key Performance Parameters

Parameter	Value	Unit
V_{DS}	150	V
$R_{DS(on),max}$	11	m Ω
I_D	77	A
Q_{rr}	46	nC



RoHS

Type / Ordering Code	Package	Marking	Related Links
BSC110N15NS5SC	PG-WSON-8	110N15SC	-

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1 Maximum ratings

at $T_A=25\text{ °C}$, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current ¹⁾	I_D	-	-	77 55	A	$T_C=25\text{ °C}$ $T_C=100\text{ °C}$
Pulsed drain current ²⁾	$I_{D,pulse}$	-	-	308	A	$T_C=25\text{ °C}$
Avalanche energy, single pulse ³⁾	E_{AS}	-	-	90	mJ	$I_D=50\text{ A}$, $R_{GS}=25\ \Omega$
Gate source voltage	V_{GS}	-20	-	20	V	-
Power dissipation	P_{tot}	-	-	150	W	$T_C=25\text{ °C}$
Operating and storage temperature	T_j, T_{stg}	-55	-	175	°C	IEC climatic category; DIN IEC 68-1: 55/175/56

2 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case, bottom	R_{thJC}	-	0.6	1.0	K/W	-
Thermal resistance, junction - case, top	R_{thJC}	-	0.36	0.72	K/W	-
Thermal resistance, junction - ambient, 6 cm ² cooling area ⁴⁾	R_{thJA}	-	-	50	K/W	-

¹⁾ Rating refers to the product only with datasheet specified absolute maximum values, maintaining case temperature as specified. For other case temperatures please refer to Diagram 2. De-rating will be required based on the actual environmental conditions.

²⁾ See Diagram 3 for more detailed information

³⁾ See Diagram 13 for more detailed information

⁴⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

3 Electrical characteristics

at $T_j=25\text{ °C}$, unless otherwise specified

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	150	-	-	V	$V_{GS}=0\text{ V}$, $I_D=1\text{ mA}$
Gate threshold voltage	$V_{GS(th)}$	3	3.8	4.6	V	$V_{DS}=V_{GS}$, $I_D=91\text{ }\mu\text{A}$
Zero gate voltage drain current	I_{DSS}	-	0.1 10	1 100	μA	$V_{DS}=120\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=25\text{ °C}$ $V_{DS}=120\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=125\text{ °C}$
Gate-source leakage current	I_{GSS}	-	1	100	nA	$V_{GS}=20\text{ V}$, $V_{DS}=0\text{ V}$
Drain-source on-state resistance	$R_{DS(on)}$	-	9 10	11 13	m Ω	$V_{GS}=10\text{ V}$, $I_D=38\text{ A}$ $V_{GS}=8\text{ V}$, $I_D=19\text{ A}$
Gate resistance	R_G	-	0.9	1.35	Ω	-
Transconductance	g_{fs}	29	58	-	S	$ V_{DS} >2 I_D R_{DS(on)max}$, $I_D=38\text{ A}$

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance	C_{iss}	-	2080	2770	pF	$V_{GS}=0\text{ V}$, $V_{DS}=75\text{ V}$, $f=1\text{ MHz}$
Output capacitance ¹⁾	C_{oss}	-	515	685	pF	$V_{GS}=0\text{ V}$, $V_{DS}=75\text{ V}$, $f=1\text{ MHz}$
Reverse transfer capacitance ¹⁾	C_{rss}	-	13	23	pF	$V_{GS}=0\text{ V}$, $V_{DS}=75\text{ V}$, $f=1\text{ MHz}$
Turn-on delay time	$t_{d(on)}$	-	10.3	-	ns	$V_{DD}=75\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=38\text{ A}$, $R_{G,ext}=3\text{ }\Omega$
Rise time	t_r	-	3.3	-	ns	$V_{DD}=75\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=38\text{ A}$, $R_{G,ext}=3\text{ }\Omega$
Turn-off delay time	$t_{d(off)}$	-	14.5	-	ns	$V_{DD}=75\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=38\text{ A}$, $R_{G,ext}=3\text{ }\Omega$
Fall time	t_f	-	2.9	-	ns	$V_{DD}=75\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=38\text{ A}$, $R_{G,ext}=3\text{ }\Omega$

Table 6 Gate charge characteristics²⁾

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	12	-	nC	$V_{DD}=75\text{ V}$, $I_D=38\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate to drain charge ¹⁾	Q_{gd}	-	5.8	8.7	nC	$V_{DD}=75\text{ V}$, $I_D=38\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Switching charge	Q_{sw}	-	11.5	-	nC	$V_{DD}=75\text{ V}$, $I_D=38\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate charge total ¹⁾	Q_g	-	28	35	nC	$V_{DD}=75\text{ V}$, $I_D=38\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate plateau voltage	$V_{plateau}$	-	5.8	-	V	$V_{DD}=75\text{ V}$, $I_D=38\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Output charge ¹⁾	Q_{oss}	-	78	103	nC	$V_{DD}=75\text{ V}$, $V_{GS}=0\text{ V}$

¹⁾ Defined by design. Not subject to production test

²⁾ See "Gate charge waveforms" for parameter definition

Table 7 Reverse diode

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode continuous forward current	I_S	-	-	77	A	$T_C=25\text{ °C}$
Diode pulse current	$I_{S,pulse}$	-	-	308	A	$T_C=25\text{ °C}$
Diode forward voltage	V_{SD}	-	0.88	1.2	V	$V_{GS}=0\text{ V}, I_F=38\text{ A}, T_j=25\text{ °C}$
Reverse recovery time ¹⁾	t_{rr}	-	45	90	ns	$V_R=75\text{ V}, I_F=38\text{ A}, di_F/dt=100\text{ A}/\mu\text{s}$
Reverse recovery charge ¹⁾	Q_{rr}	-	46	92	nC	$V_R=75\text{ V}, I_F=38\text{ A}, di_F/dt=100\text{ A}/\mu\text{s}$

¹⁾ Defined by design. Not subject to production test

4 Electrical characteristics diagrams

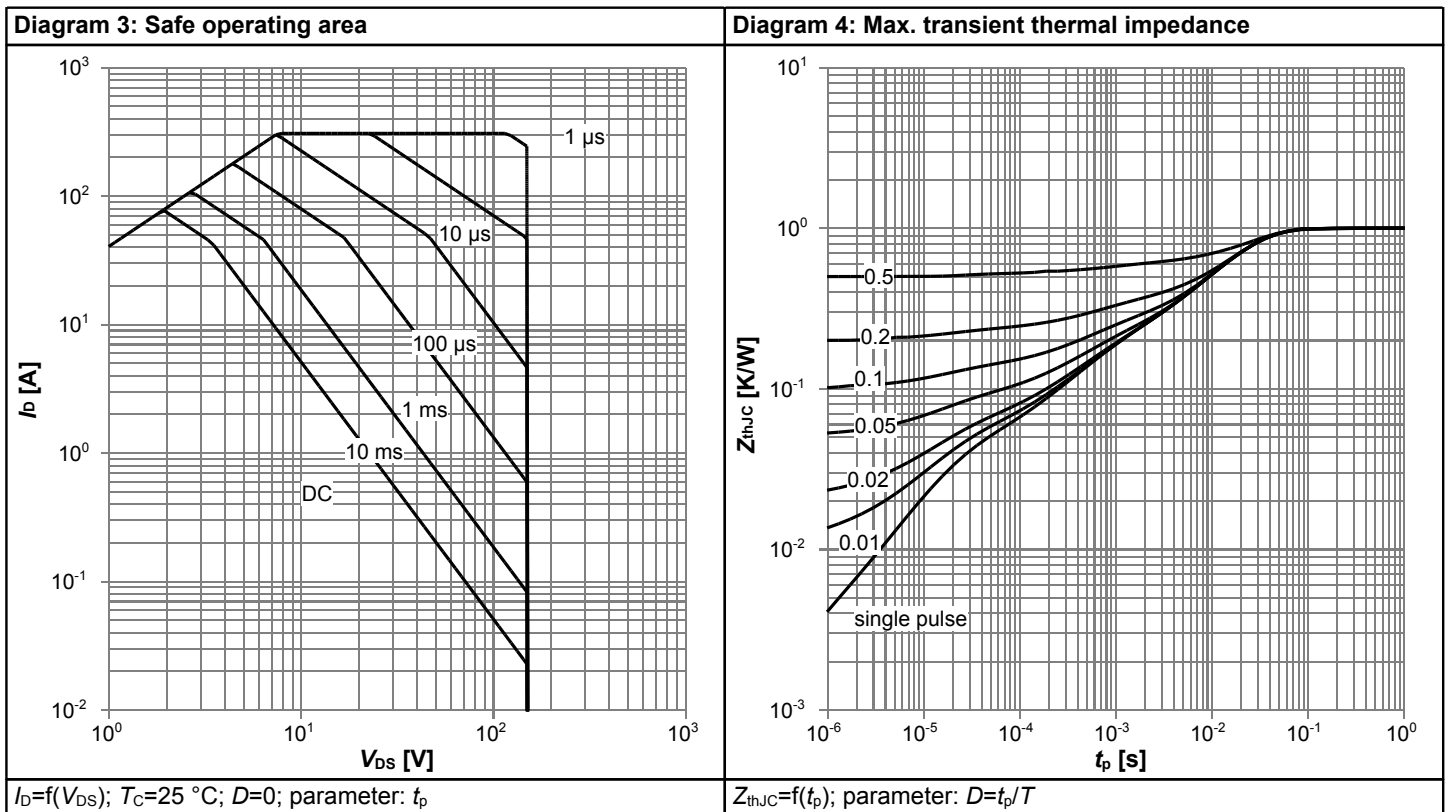
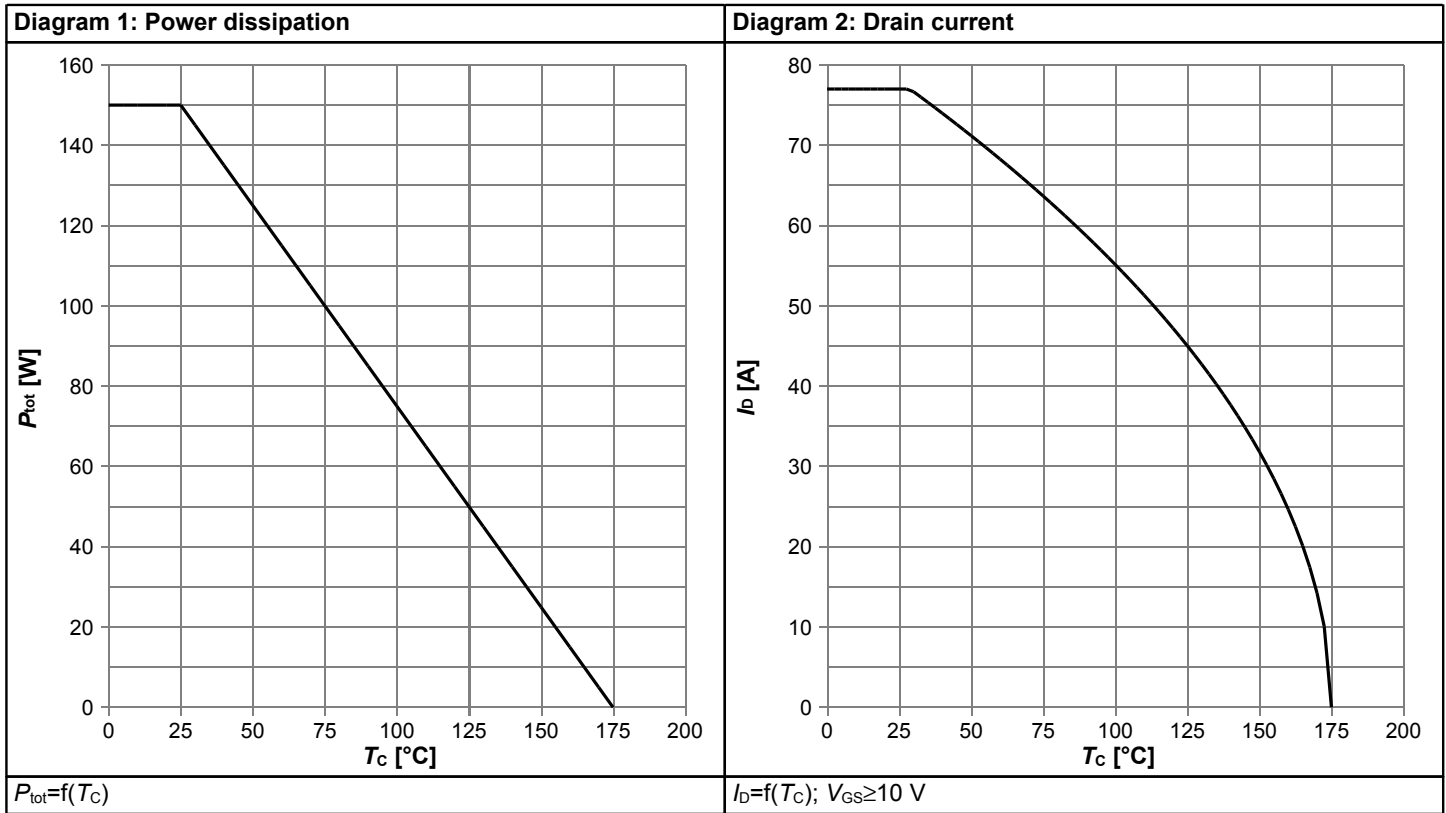
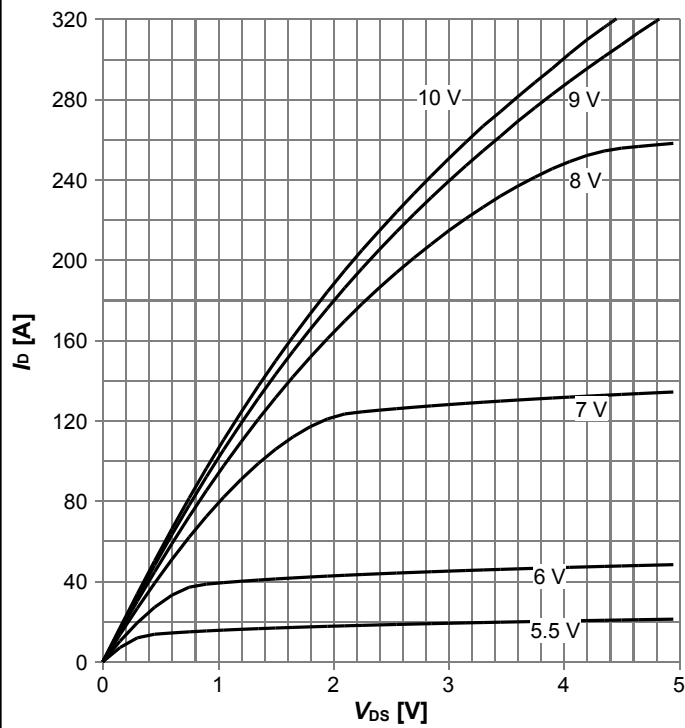
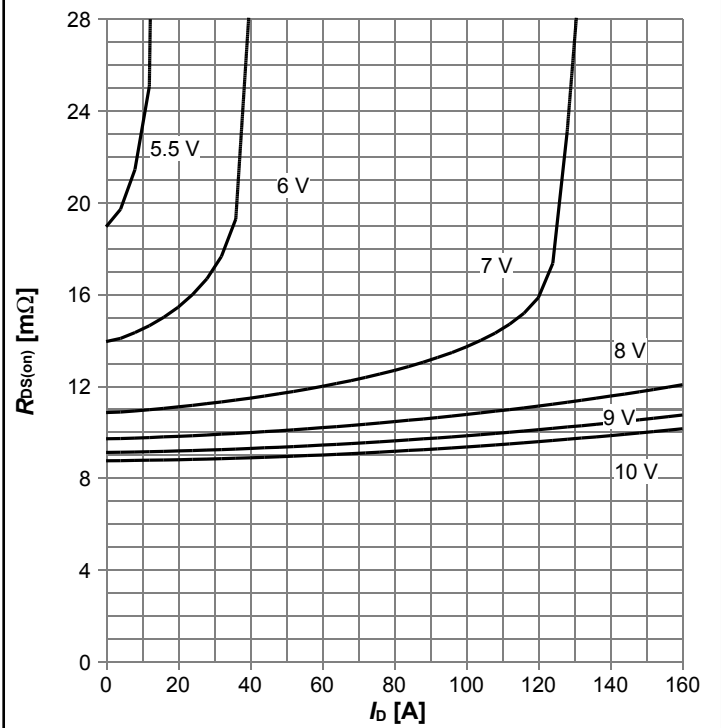


Diagram 5: Typ. output characteristics



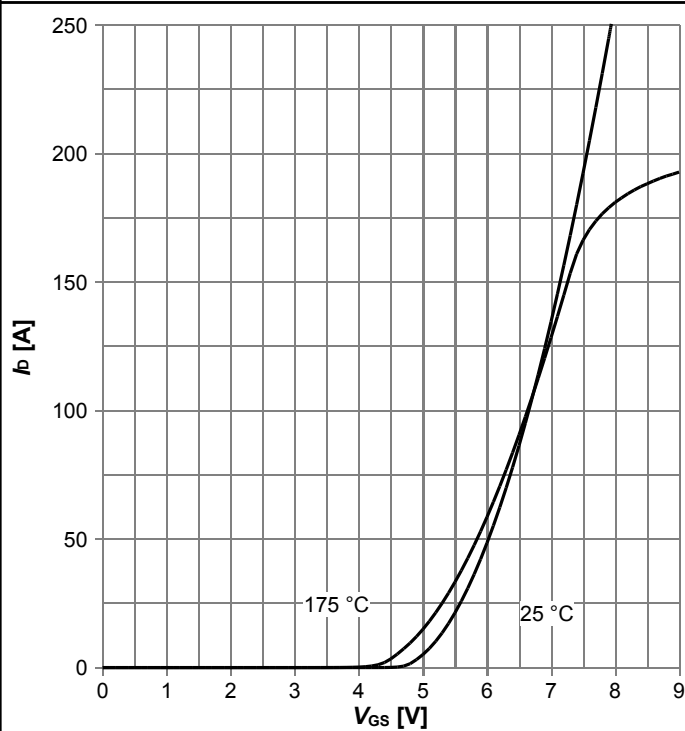
$I_D = f(V_{DS})$, $T_j = 25\text{ °C}$; parameter: V_{GS}

Diagram 6: Typ. drain-source on resistance



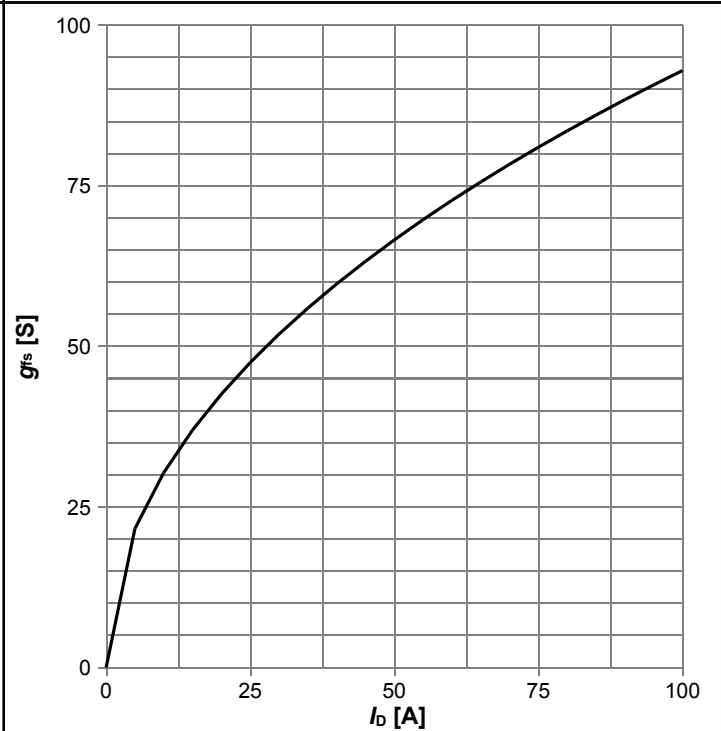
$R_{DS(on)} = f(I_D)$, $T_j = 25\text{ °C}$; parameter: V_{GS}

Diagram 7: Typ. transfer characteristics



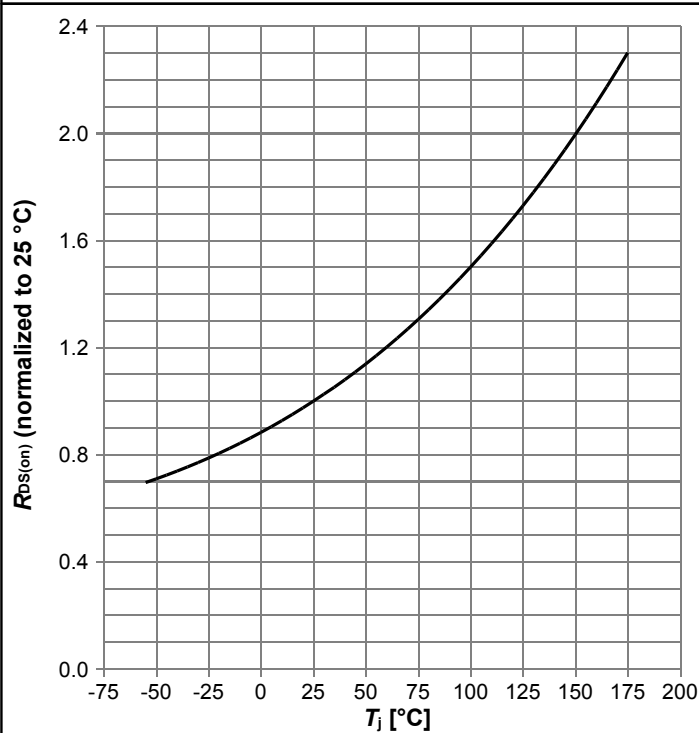
$I_D = f(V_{GS})$, $|V_{DS}| > 2|I_D|R_{DS(on)max}$; parameter: T_j

Diagram 8: Typ. forward transconductance



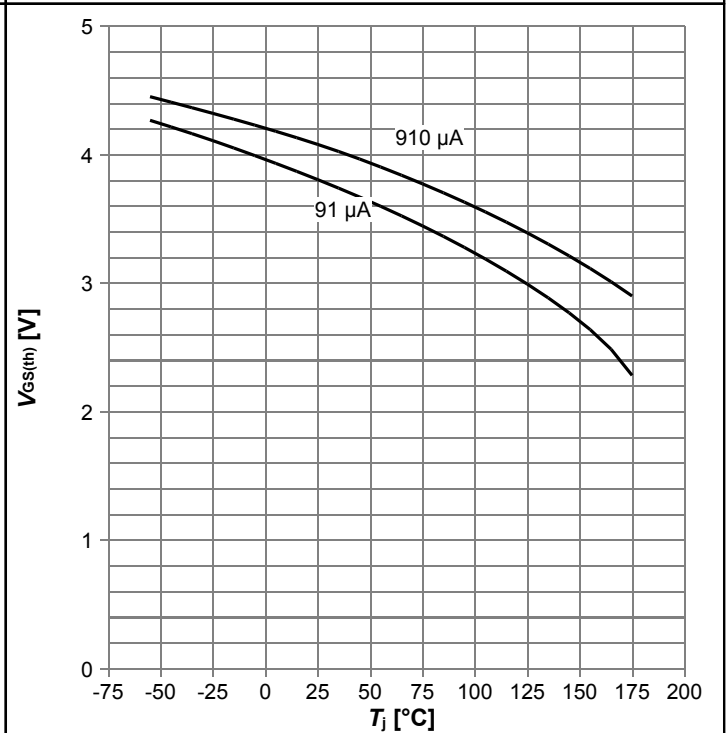
$g_{fs} = f(I_D)$; parameter: V_{DS} , T_j

Diagram 9: Drain-source on-state resistance



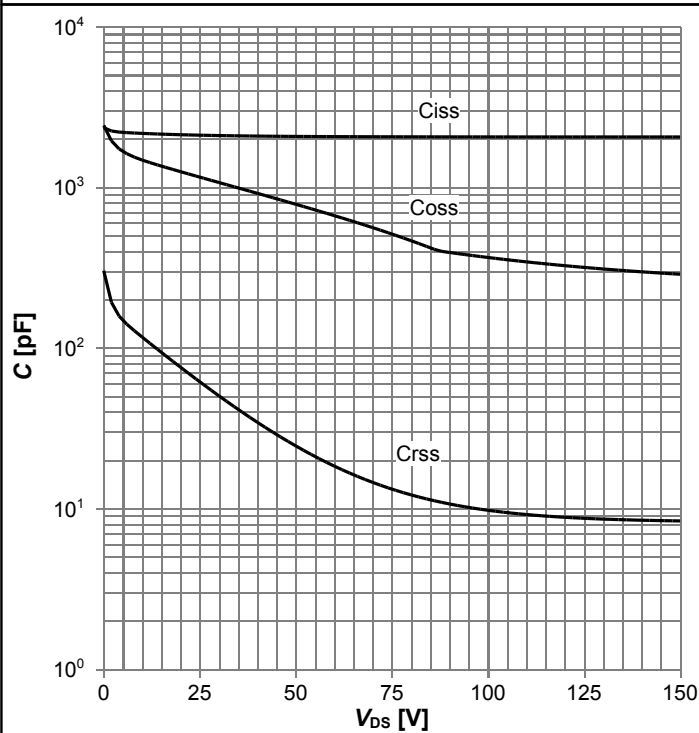
$R_{DS(on)}=f(T_j)$, $I_D=38$ A, $V_{GS}=10$ V

Diagram 10: Typ. gate threshold voltage



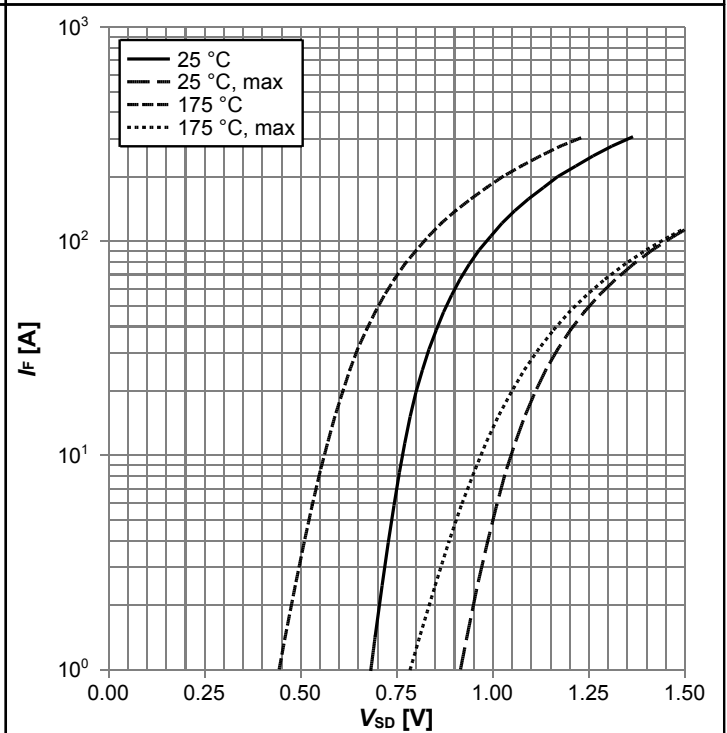
$V_{GS(th)}=f(T_j)$, $V_{GS}=V_{DS}$; parameter: I_D

Diagram 11: Typ. capacitances



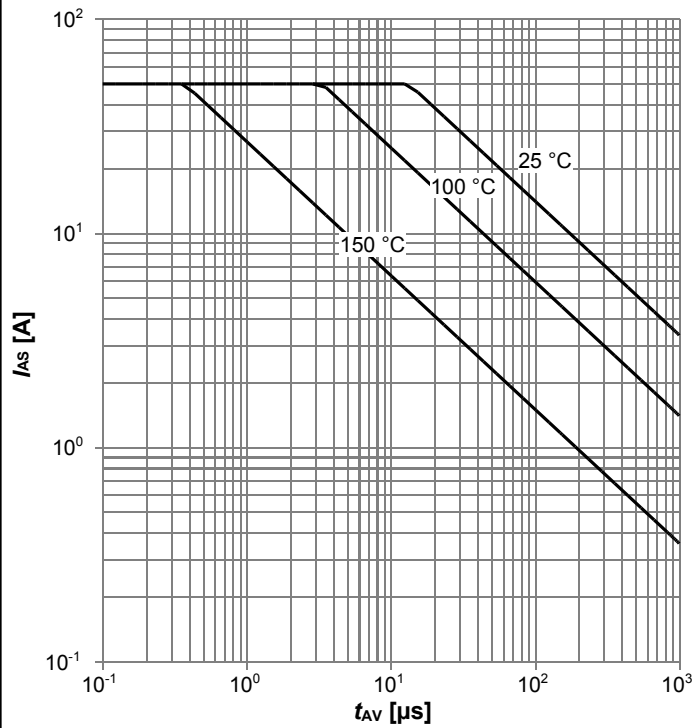
$C=f(V_{DS})$; $V_{GS}=0$ V; $f=1$ MHz

Diagram 12: Forward characteristics of reverse diode



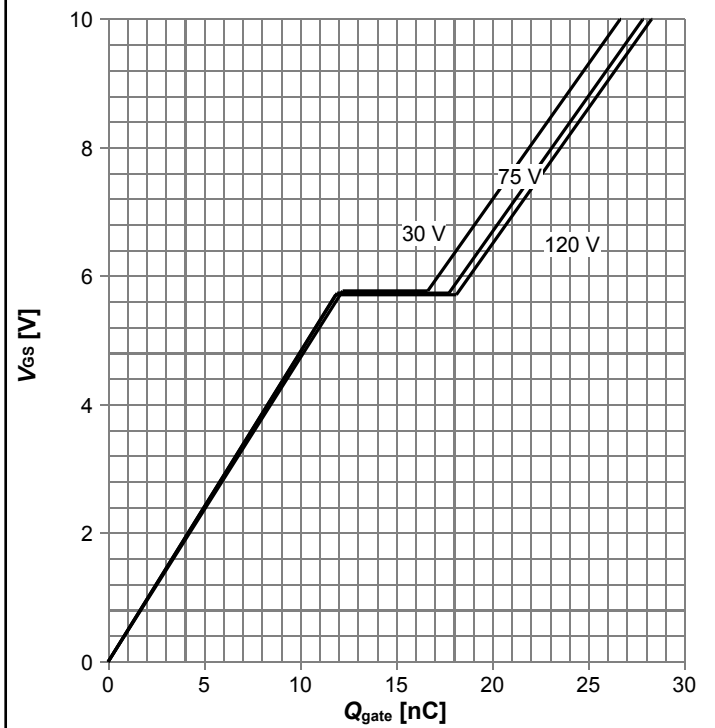
$I_F=f(V_{SD})$; parameter: T_j

Diagram 13: Avalanche characteristics



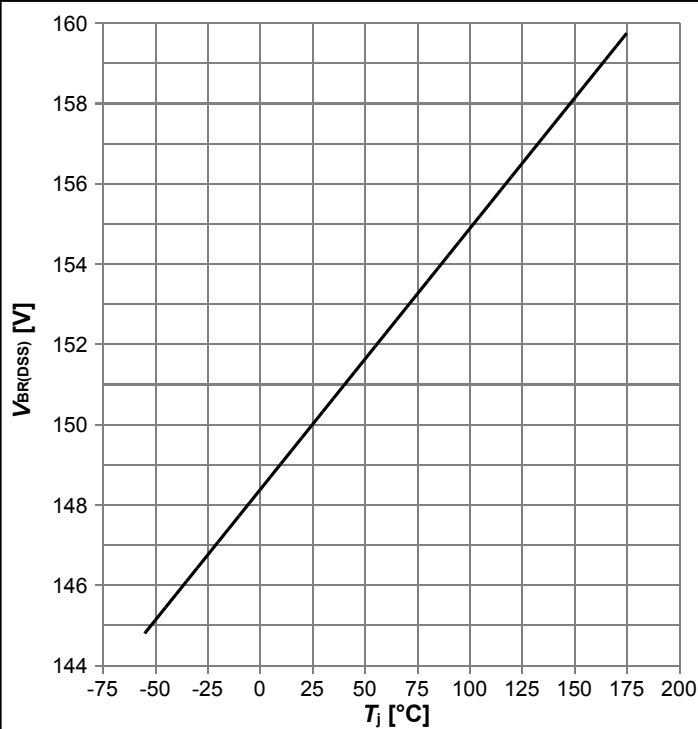
$I_{AS}=f(t_{AV}); R_{GS}=25 \Omega$; parameter: $T_{j,start}$

Diagram 14: Typ. gate charge



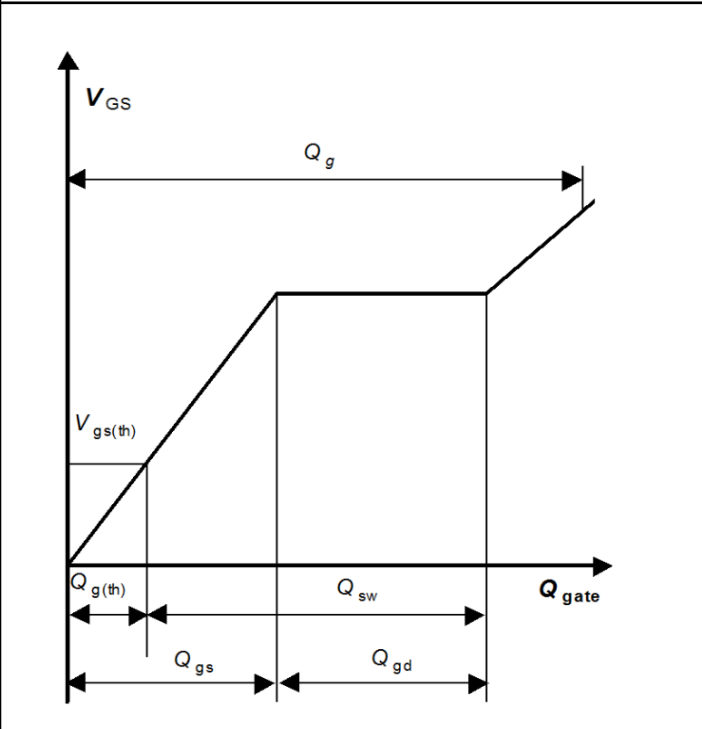
$V_{GS}=f(Q_{gate}), I_D=38 \text{ A pulsed}, T_j=25 \text{ °C}$; parameter: V_{DD}

Diagram 15: Drain-source breakdown voltage

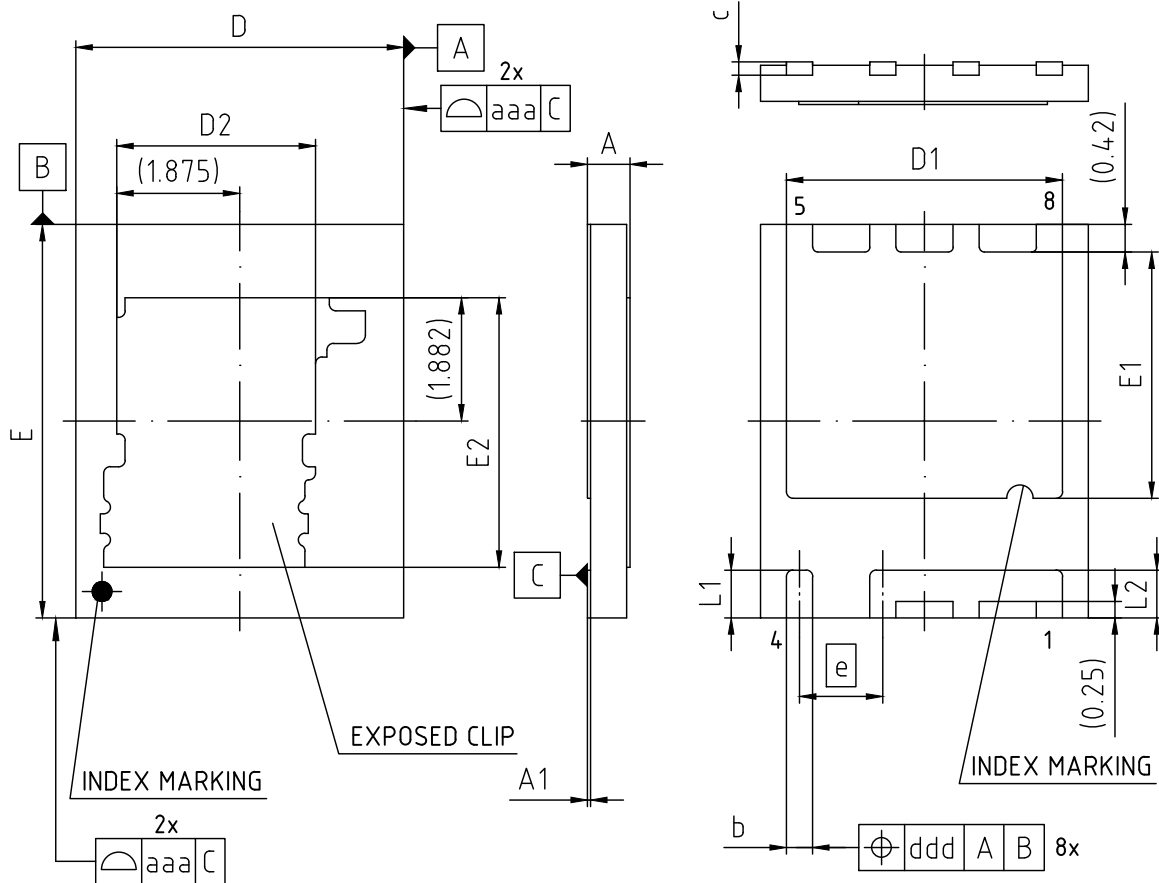


$V_{BR(DSS)}=f(T_j); I_D=1 \text{ mA}$

Diagram Gate charge waveforms



5 Package Outlines



DIMENSIONS DOES NOT INCLUDE MOLD FLASH OR MOLD PROTRUSIONS.

DIMENSION	MILLIMETERS	
	MIN.	MAX.
A	-	0.75
A1	-	0.05
b	0.35	0.45
c	0.203	
D	4.95	5.05
D1	4.11	4.31
D2	3.03	
E	5.95	6.05
E1	3.66	3.86
E2	4.11	
e	1.27	
L1	0.675	0.775
L2	0.625	0.825
aaa	0.05	
ddd	0.10	

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Figure 1 Outline PG-WSON-8, dimensions in mm

Revision History

BSC110N15NS5SC

Revision: 2022-10-07, Rev. 2.1

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.0	2022-09-17	Release of final version
2.1	2022-10-07	Update "Features"

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